

STRUCTURE

Silicon Monolithic Integrated Circuit

TYPE

8 Channel Switching Regulator Controller and 1 Series Regulator for DVC

PRODUCT SERIES

BD9833KV

FEATURES

• 8 DC/DC controller,1 Series Regulator

- DC/DC controller: FET direct driver (Pch driver:7ch, Nch driver:1ch)

 Series Regulator: Variable output voltage stable with Ceramic Output Capacitor
 Package: VQFP48C(0.5mm pitch)

○Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Units
Power Supply Voltage1	VCC,VIN2345,VIN6789	12	V
Power Supply Voltage2	VIN1	12	V
Power Dissipation	Pd	600(*1) 950(*2)	mW mW
Operating Temperature	Topr	-25~+85	င
Storage Temperature	Tstg	-55 ~ +125	ဇ

^(*1) Without external heat sink, the power dissipation degrades by 6.0mW/°C above 25°C.

○Recommended operating conditions (Ta=-25~+75°C)

Parameter	Symbol	Spec.	Units
Power Supply Voltage	VCC,VIN2345,VIN6789 VIN1	4.0~10 2.8~10	V
Oscillator Frequency	fosc	100kHz~1.2MHz	

Status of this document

The Japanese version of this document is the official specification.

Please use the translation version of this document as a reference to expedite understanding of the official version.

If these is any uncertainty in translation version of this document, official version takes priority.

^(*2) Power dissipation degrades by 9.5mW/°C above 25°C, when mounted on a PCB (70.0mm × 70.0mm × 1.6mm).

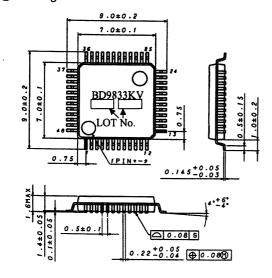


○Electrical characteristics (Ta=25°C, VCC=7V, VIN1=7V STB=3V, unless otherwise specified)

				1 D=3 V	, uniess otherwise sp		
Symbol		Spec.		Units	Conditions.		
Cymbol	Min.	Тур.	Max		Conditions.		
Vref	2.475	2.500	2.525	V	•		
DVLi	<u> </u>	-	10	mV	Vcc=4.0V~10V		
DVLo	-	-	10	mV	Iref=-0.1mA∼ -1.0mA		
los	-40	-12	-5	mA	Vref=0V		
Short-Circuit Output Current los -40 -12 -5 mA Vref=0V [Load Regulation]							
Vstd1	3.55	3.65	3.75	٧	VCC monitor		
					Sweep down		
ΔVst1	0.6	0.11	0.16	٧			
Vstd2	2.2	2.3	2.4	V	VREF monitor		
ISOF11	-2.0	-1.0	-0.5	μΑ			
					CH2 2 4 5 6 7		
Vscpth	0.65	0.75	0.85	v	CH2,3,4,5,6,7, INV Voltage"L" detect		
Iscp	-3.0	-2.0	-1.5	μΑ	VSCP=0.75V		
Vtsc	1.4	1.5	1.6	V			
Vssc		10	100	mV			
fosc	580	680	780	kHz	RT=11kohm,CT=180pF		
Df		0.3	2	%	VCC=4.0~10V		
VRT	0.95	1.00	1.05	V			
T							
Vthea	0.980	1.00	1.020	V	CH2,3,4,5,6,7		
	· .	-	10	mV	CH8,9		
	-150	0	150	nA	CH2,3,4,5,6,7 INV pin		
	-170	-40	<u> </u>	nA	CH8,9 INV pin		
lbias3	-170	-40		nA	CH8,9 NON pin		
AV	50	65	80	dB	DC Design		
DW.	0.5			NAL 1-	Guarantee AV=0dB		
		1	2	MHZ	Design Guarantee		
VIDII		-	-	V			
Vfbl	-		0.1	V			
Isink1	1.3	2.6					
lsink2	3.4		10				
Isource1	-240	-150	-90	μΑ			
Isource2	-280	-190	-130	μΑ			
VCM	0		VCC-2	٧			
					_		
Vt0	1.730	1.820	1.910	V	DUTYO%		
Vt100	2.090	2.180	2.270	٧	DUTY100%		
RonHI1 RonL01	7	14	21	Ω	VG2, 3, 4, 5, 6, 7, 8, 9 VG="H"		
r KONLOT	. 6						
			18 250	Ω	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L"		
Isink1 Isource1	70 -240	170 -160	18 250 -80	Ω mA mA			
Isink1 Isource1	70	170	250	mA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L"		
Isink1 Isource1 Vstb	70 -240	170 -160	250 -80	mA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L"		
Isink1 Isource1 Vstb Istb	70 -240	170 -160	250 -80 2. 0 30	mA mA V μA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L"		
Isink1 Isource1 Vstb Istb Vstb5, 6	70 -240 1.0 - 1.0	170 -160 1.5 - 1.5	250 -80 2. 0 30 2. 0	mA mA V μA V	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V		
Isink1 Isource1 Vstb Istb	70 -240	170 -160	250 -80 2. 0 30	mA mA V μA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H"		
Isink1 Isource1 Vstb Istb Vstb5,6 Istb5,6	70 -240 1.0 - 1.0	170 -160 1.5 - 1.5	250 -80 2.0 30 2.0 30	mA mA V μ A V μ A	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB5, 6=3V		
Isink1 Isource1 Vstb Istb Vstb5,6 Istb5,6	70 -240 1.0 - 1.0 -	170 -160 1.5 - 1.5 -	250 -80 2.0 30 2.0 30	mA mA V μ A V μ A	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V		
Isink1 Isource1 Vstb Istb Vstb5,6 Istb5,6	70 -240 1.0 - 1.0	170 -160 1.5 - 1.5	250 -80 2.0 30 2.0 30	mA mA V μ A V μ A	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB5, 6=3V		
Isink1 Isource1 Vstb Istb Vstb5,6 Istb5,6 Iccs Icc	70 -240 1.0 - 1.0 - 1.1	170 -160 1.5 - 1.5 - 0 5	250 -80 2.0 30 2.0 30	mA mA V μA V μA μA mA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB5, 6=3V		
Isink1 Isource1 Vstb Istb Vstb5, 6 Istb5, 6 Iccs Icc Vo1	70 -240 1.0 - 1.0 - 1	170 -160 1.5 - 1.5 - 0 5	250 -80 2. 0 30 2. 0 30 5 10	mA mA V μ A V μ A μ A MA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB5, 6=3V		
Isink1	70 -240 1.0 - 1.0 - 1 1 2.94 0.98	170 -160 1.5 - 1.5 - 0 5 3.00	250 -80 2.0 30 2.0 30 5 10	mA mA V μA V μA V μA V V μ V V V	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB5, 6=3V STB=0V R1=200KΩ, R2=100KΩRefer to below		
Isink1 Isource1 Vstb Istb Vstb5,6 Istb5,6 Iccs Icc Vo1 VFB1 Io1	70 -240 1.0 - 1.0 - 1	170 -160 1.5 - 1.5 - 0 5	250 -80 2. 0 30 2. 0 30 5 10	mA mA V μ A V μ A μ A MA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB5, 6=3V STB=0V R1=200KΩ, R2=100KΩRefer to below figure		
Isink1	70 -240 1.0 - 1.0 - 1 1 2.94 0.98	170 -160 1.5 - 1.5 - 0 5 3.00	250 -80 2.0 30 2.0 30 5 10	mA mA V μA V μA V μA V V μ V V V	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB=0V R1=200KΩ, R2=100KΩRefer to below figure VIN1=VOUT1x0.97, 10UT1=20mA		
Isink1 Isource1 Vstb Istb Vstb5, 6 Istb5, 6 Iccs Icc Vo1 VFB1 Io1 Io1	70 -240 1.0 - 1.0 - 1.0 - 1 1 2.94 0.98 300	170 -160 1.5 - 1.5 - 0 5 3.00 1.00	2:0 -80 2:0 30 2:0 30 5 10 3.06	mA mA V μA V μΔ M mA V V μΑ M MA M	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB5, 6=3V STB-0V R1=200KΩ, R2=100KΩRefer to below figure VIN1=VOUT1x0.97, 10UT1=20mA VIN1=4V to10V 10UT1=100mA		
Isink1	70 -240 1.0 - 1.0 - 1 1 2.94 0.98 300 70	170 -160 1.5 - 1.5 - 1.5 - 0 5 3.00 1.00 -	250 -80 2.0 30 2.0 30 5 10 3.06 1.02 -	mA mA V μA V μA MA V ν μ A mA mA	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB=0V R1=200KΩ, R2=100KΩRefer to below figure VIN1=V0UT1x0.97, 10UT1=20mA VIN1=4V to10V 10UT1=100mA VIN1=3, 5V to10V 10UT1=10mA		
Isink1 Isource1	70 -240 1.0 - 1.0 - 1.0 - 1 2.94 0.98 300 70	170 -160 1.5 - 1.5 - 1.5 - 3.00 1.00 - 120	2:50 -80 2:0 30 2:0 30 5 10 3.06 1.02 - 2:50	mA mA V μ A V μ A V μ A V ν α Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ Μ	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB=3V STB=0V R1=200KΩ, R2=100KΩRefer to below figure VIN1=VOUT1x0.97, 10UT1=20mA VIN1=4V to10V 10UT1=10mA VIN1=10mA 10UT1=10mA 10UT1=1mA to 100mA		
Isink1 Isource1	70 -240 1.0 - 1.0 - 1.0 - 1 2.94 0.98 300 70 - -	170 -160 -1.5 - 1.5 - 1.5 - 0 5 - 3.00 - 120 - 4 4	250 -80 -80 2.0 30 2.0 30 5 10 3.06 1.02 - 250 10 10	mA mA V μA V μA V μA V ν μ A mA mA V V mA mV mV	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB=3V STB=0V R1=200KΩ, R2=100KΩRefer to below figure VIN1=V0UT1x0.97, 10UT1=20mA VIN1=4V to10V 10UT1=100mA IOUT1=10mA IOUT1=1mA to 100mA IOUT1=1mA to 300mA		
Isink1 Isource1	70 -240 1.0 - 1.0 - 1.0 - 1 2.94 0.98 300 70	170 -160 -1.5 - 1.5 - 1.5 - 3.00 1.00 - 120 4	250 -80 -80 2.0 30 2.0 30 5 10 3.06 1.02 - 250 10	mA mA V μA V μA V μA V ν μ A mA mA V V mA mV mV	VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="L" VG2, 3, 4, 5, 6, 7, 8, 9 VG="H" STB=3V STB=0V R1=200KΩ, R2=100KΩRefer to below figure VIN1=VOUT1x0. 97, 10UT1=20mA VIN1=4V to10V 10UT1=10mA VIN1=3. 5V to10V 10UT1=10mA 10UT1=1mA to 100mA		
	DVLi DVLo los Vstd1 Δ Vstd1 Vstd2 Vsso1 ISOFT1 Vscpth Iscp Vtsc Vssc Fosc Df VRT Vthea VOFST Ibias1 Ibias2 Ibias3 AV BW Vfbh Vfbl Isink1 Isink2 Isource1 Isource2 VCM	DVLi - DVLo - los -40 Vstd1 3.55 Δ Vst1 0.6 Vstd2 2.2 Vsso1 - ISOFT1 -2.0 Vscpth 0.65 Iscp -3.0 Vtsc 1.4 Vssc - fosc 580 Df - VRT 0.95 Vthea 0.980 VOFST - Ibias1 -150 Ibias2 -170 Ibias3 -170 AV 50 BW 0.5 Vfbh Vref -0.1 Vfbl - Isink1 1.3 Isink2 3.4 Isource1 -240 Isource2 -280 VCM 0	DVLi	DVLi - - 10 DVLo - - 10 Ios -40 -12 -5 Vstd1 3.55 3.65 3.75 ΔVst1 0.6 0.11 0.16 Vstd2 2.2 2.3 2.4 Vsso1 - 10 100 ISOFT1 -2.0 -1.0 -0.5 Vscpth 0.65 0.75 0.85 Iscp -3.0 -2.0 -1.5 Vtsc 1.4 1.5 1.6 Vssc - 10 100 fosc 580 680 780 Df - 0.3 2 VRT 0.95 1.00 1.05 Vthea 0.980 1.00 1.020 VOFST - - 10 Ibias1 -150 0 150 Ibias2 -170 -40 - Ibias3 -170	DVLi - - 10 mV DVLo - - 10 mV Ios -40 -12 -5 mA Vstd1 3.55 3.65 3.75 V ΔVst1 0.6 0.11 0.16 V Vstd2 2.2 2.3 2.4 V Vsso1 - 10 100 mV ISOFT1 -2.0 -1.0 -0.5 μA Vscpth 0.65 0.75 0.85 V Iscp -3.0 -2.0 -1.5 μA Vtsc 1.4 1.5 1.6 V Vssc - 10 100 mV fosc 580 680 780 kHz Df - 0.3 2 % VRT 0.95 1.00 1.05 V Vfea 0.980 1.00 1.020 V VOFST - <t< td=""></t<>		

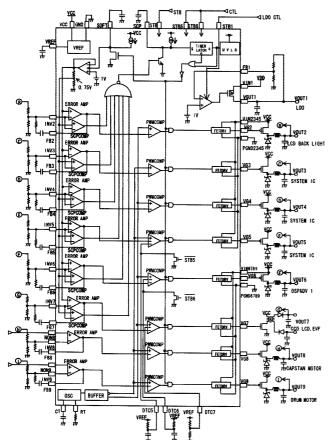
ROHM

OPackage Dimensions



VQFP48C (Unit:mm)

OBlock Diagram



OPin Description

番号	Description 端子名 機能		
1	INV5	機能 Error Amp inverted input(CH5)	
2	FB5	Error Amp output (CH5)	
3	INV6	Error Amp inverted input (CH6)	
4	FB6	Error Amp output (CH6)	
5	INV7	Error Amp inverted input(CH7)	
		Error Amp output (CH7)	
7	FB7	Error Amp non-inverted input (CH8)	
	NON8	Error Amp inverted input(CH8)	
9	INV8	Error Amp output (CH8)	
10	FB8		
	NON9	Error Amp inverted input (CH9)	
11	INV9	Error Amp cutout (CH9)	
12	FB9	Error Amp output (CH9)	
13	VG9	FET Driver Output (CH9)	
14	VG8	FET Driver Output (CH8)	
15	V1N6789	Power supply for the output circuit (CH6,7,8,9)	
16	PGND6789	Power Ground for the output circuit (CH6,7,8,9)	
17	VG7	FET Driver Output (CH7)	
18	VG6	FET Driver Output (CH6)	
19	VG5	FET Driver Output (CH5)	
20	VG4	FET Driver Output (CH4)	
21	V1N2345	Power supply for the output circuit (CH2,3,4,5)	
22	PGND2345	Power Ground for the output circuit (CH2,3,4,5)	
23	VG3	FET Driver Output (CH3)	
24	VG2	FET Driver Output (CH2)	
25	FB2	Error Amp output (CH2)	
26	INV2	Error Amp inverted input(CH2)	
27	FB3	Error Amp output (CH3)	
28	INV3	Error Amp inverted input(CH3)	
29	STB	SW for CH2~9, Hi:Operating	
30	GND	Ground	
31	FB4	Error Amp output (CH4)	
32	INV4	Error Amp inverted input(CH4)	
33	STB5	SW for CH5, Hi:Operating	
34	STB6	SW for CH6, Hi:Operating	
35	STB1	SW for CH1, Hi:Operating	
36	VOUT1	Series Regulator Output	
37	VIN1	Power supply for Series Regulator	
38	FB1	Amp inverted input	
39	N.C.	Non-Connected pin	
40	SCP	A capacitor is placed to set up the delay time of the SCP	
41	SOFT	Soft start/This pin connects to a capacitor to set up the start-up time	
42	VREF	Reference Voltage Output pin	
43	vcc	Power supply for DC/DC	
44	СТ	A capacitor is to set up the triangular-wave frequency	
45	RT	A resistor is to set up the triangular-wave frequency	
46	DTC5	Dead time control pin for CH5	
47	DTC6	Dead time control pin for CH6	
	DTC7	Dead time control pin for CH7.And this pin connects to a	



1) Absolute maximum ratings

Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC deterioration or damage. Assumptions should not be made regarding the state of the IC (short mode or open mode) when such damage is suffered. A physical safety measure such as a fuse should be implemented when use of the IC in a special mode where the absolute maximum ratings may be exceeded is anticipated.

Ensure a minimum GND pin potential in all operating conditions. In addition, ensure that no pins other than the GND pin carry a voltage lower than or equal to the GND pin, including during actual transient

3) Thermal design

Use a thermal design that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions.

4) Inter-pin shorts and mounting errors

Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins or between output pins and the power supply and GND pin caused by the presence of a foreign object may result in damage to the IC.

5) Operation in a strong electromagnetic field

Use caution when using the IC in the presence of a strong electromagnetic field as doing so may cause the IC to malfunction.

6) Thermal shutdown circuit (TSD circuit)

This IC incorporates a built-in thermal shutdown circuit (TSD circuit). The TSD circuit is designed only to shut the IC off to prevent runaway thermal operation. Do not continue to use the IC after operating this circuit or use the IC in an environment where the operation of the thermal shutdown circuit is assumed.

7) Testing on application boards

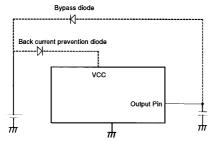
When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Ground the IC during assembly steps as an antistatic measure, and use similar caution when transporting or storing the IC. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process

8) Common impedance

Power supply and ground wiring should reflect consideration of the need to lower common impedance and minimize ripple as much as possible (by making wiring as short and thick as possible or rejecting ripple by incorporating inductance and capacitance).

9) Applications with modes that reverse VCC and pin potentials may cause damage to internal IC circuits.

For example, such damage might occur when VCC is shorted with the GND pin while an external capacitor is charged. It is recommended to insert a diode for preventing back current flow in series with VCC or bypass diodes between VCC and each pin.



10) Timing resistor

Timing resistor connected between RT and GND, has to be placed near RT terminal (45pin). With the connection must be as short as possible.

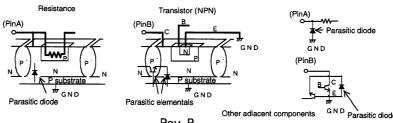
This monolithic IC contains P+ isolation and PCB layers between adjacent elements in order to keep them isolated.

P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements.

For example, when a resistor and transistor are connected to pins as shown in follow chart.

- O the P/N junction functions as a parasitic diode when GND > (Pin A) for the resistor or GND > (Pin B) for the transistor (NPN).
- O Similarly, when GND > (Pin B) for the transistor (NPN), the parasitic diode described above combines with the N layer of other adjacent elements to operate as a parasitic NPN transistor.

The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltages lower than the GND (PCB) voltage to input and output pins.



Rev. B

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